

This Page Is Inserted by IFW Operations
and is not a part of the Official Record

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

**As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.**

BEST AVAILABLE COPY

In the Drawings:

Please approve the proposed drawing revisions as shown in the attached proposed drawing sheets. Additionally, a further sectional view corresponding to Figure 5 is attached. Should the Examiner require inclusion of such a Figure in view of the following remarks, approval of the same is respectfully requested. Further, a copy of the original informal drawing of Figure 5 of the parent application 09/711,725, now U. S. Patent 6,472,258, is also attached. This informal drawing shows a surface connection by a double line above the region indicated by reference numeral 50. Should the Examiner require inclusion of this feature in Figure 5 of the present application, approval thereof is also respectfully requested.

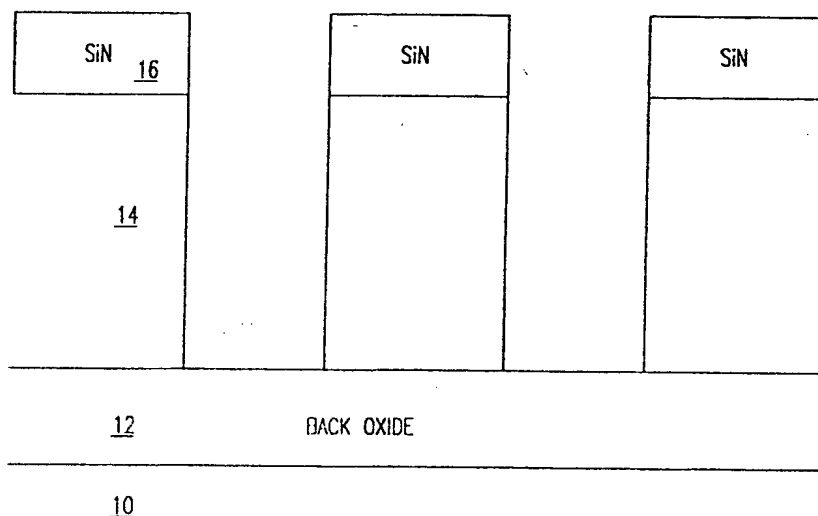


FIG. 1
(SECTION AA')

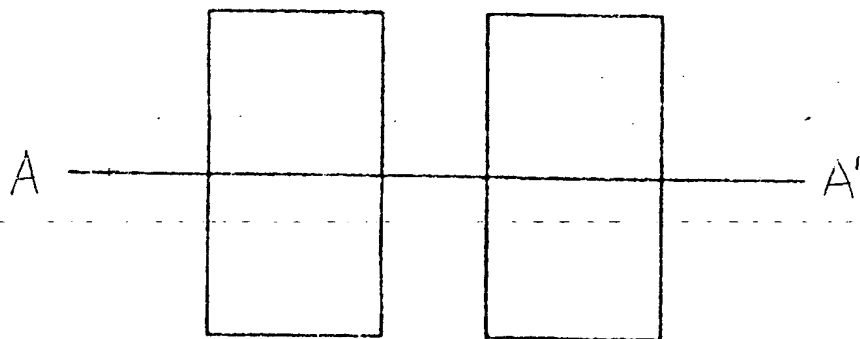


FIG. 1A

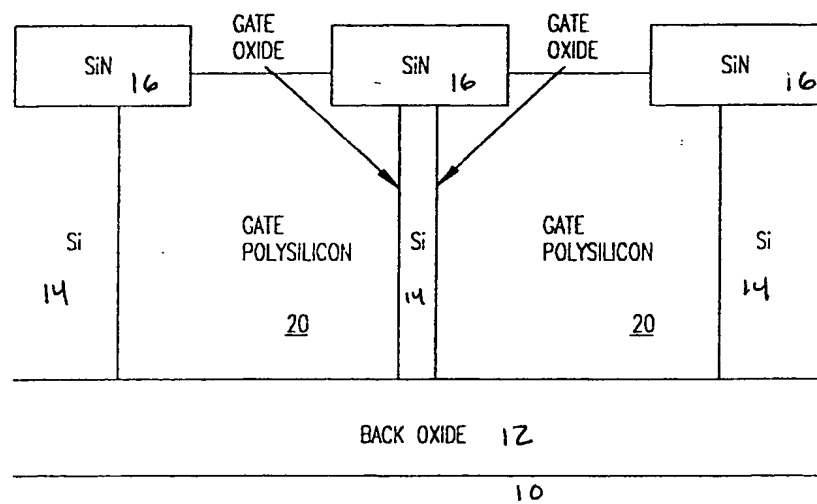


FIG. 2
(SECTION AA')

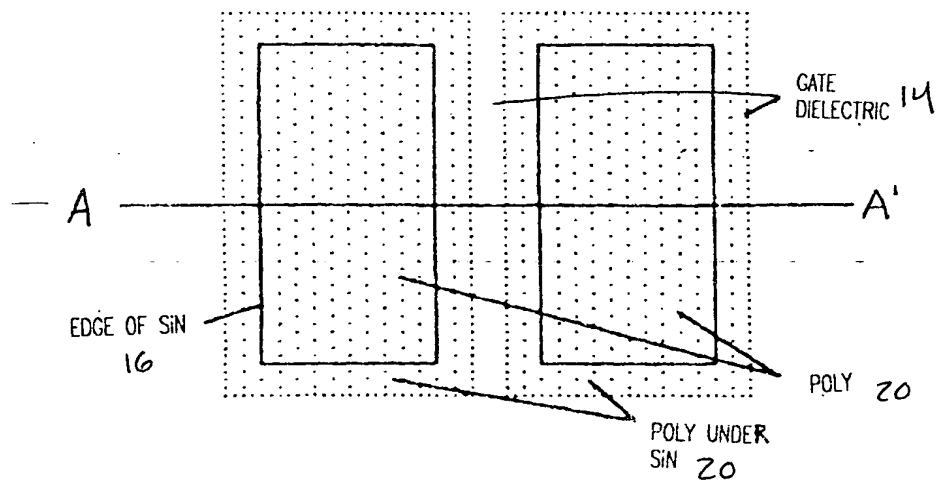


FIG. 2A

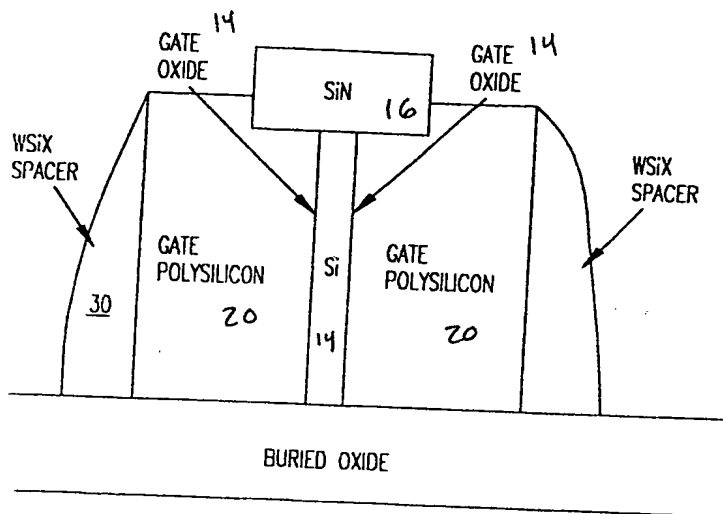


FIG. 3
(SECTION AA')

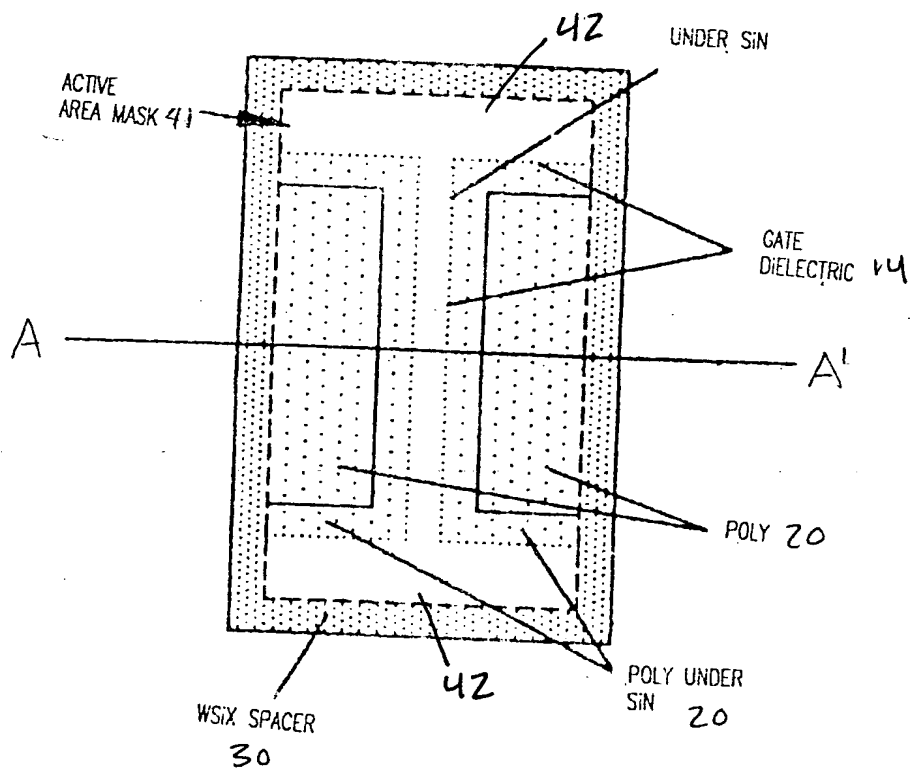


FIG. 3A

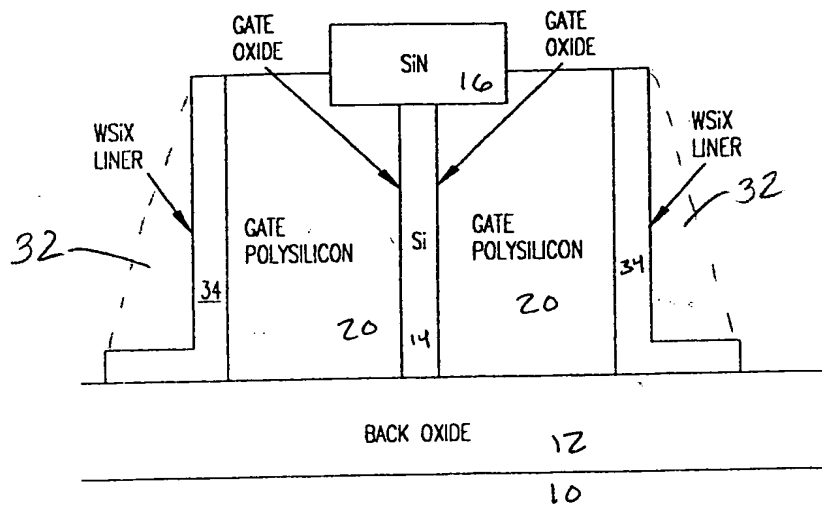


FIG. 3B
(SECTION AA')

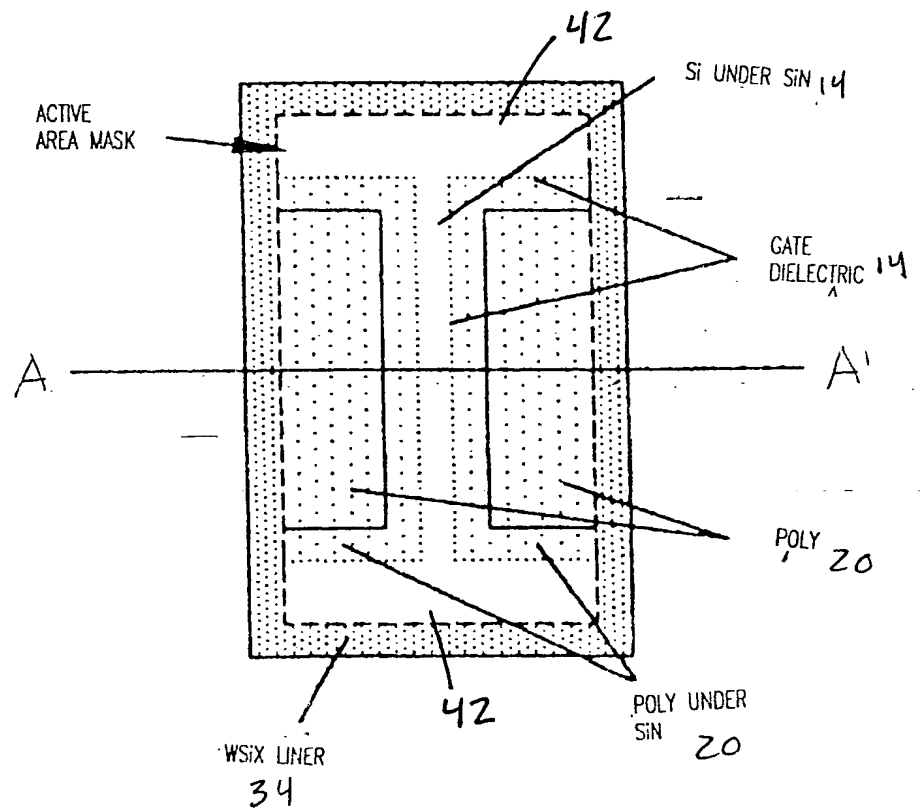


FIG. 3A

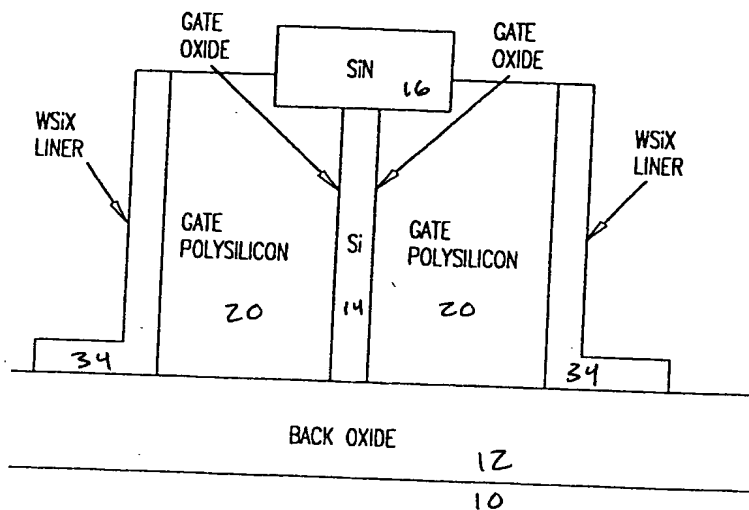


FIG. 4
(SECTION AA')

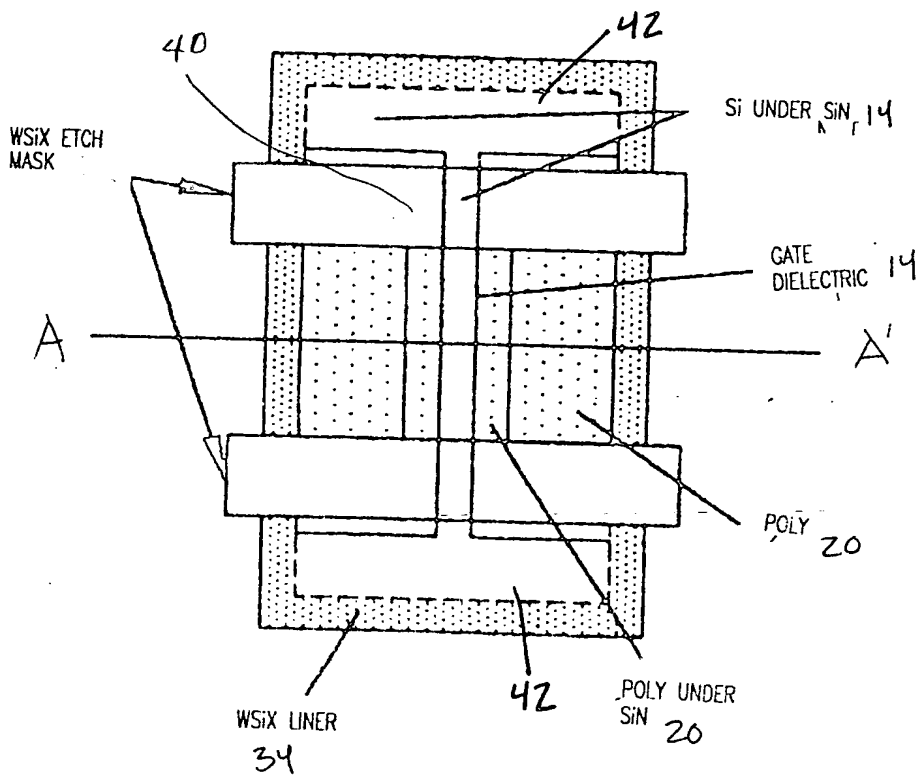


FIG. 4A

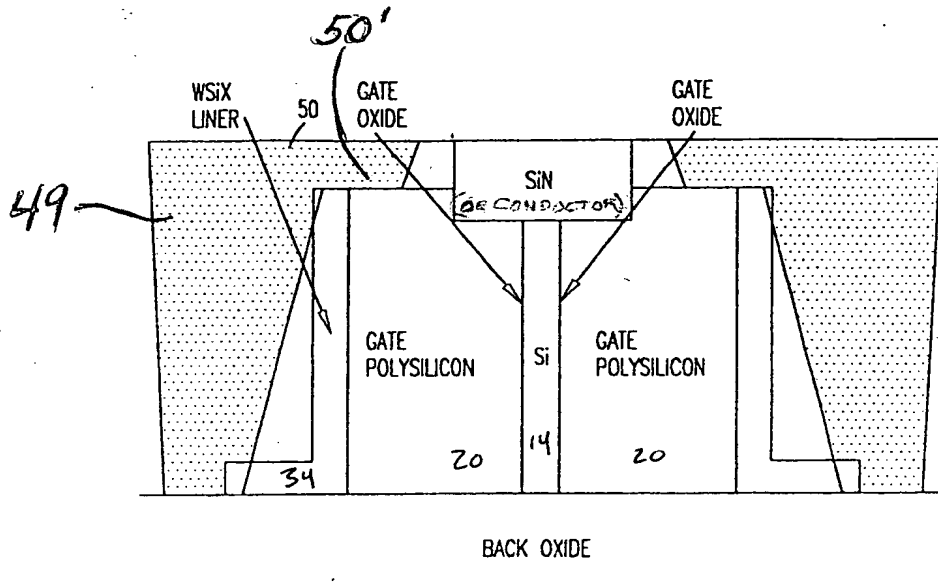


FIG. 5
(SECTION AA')

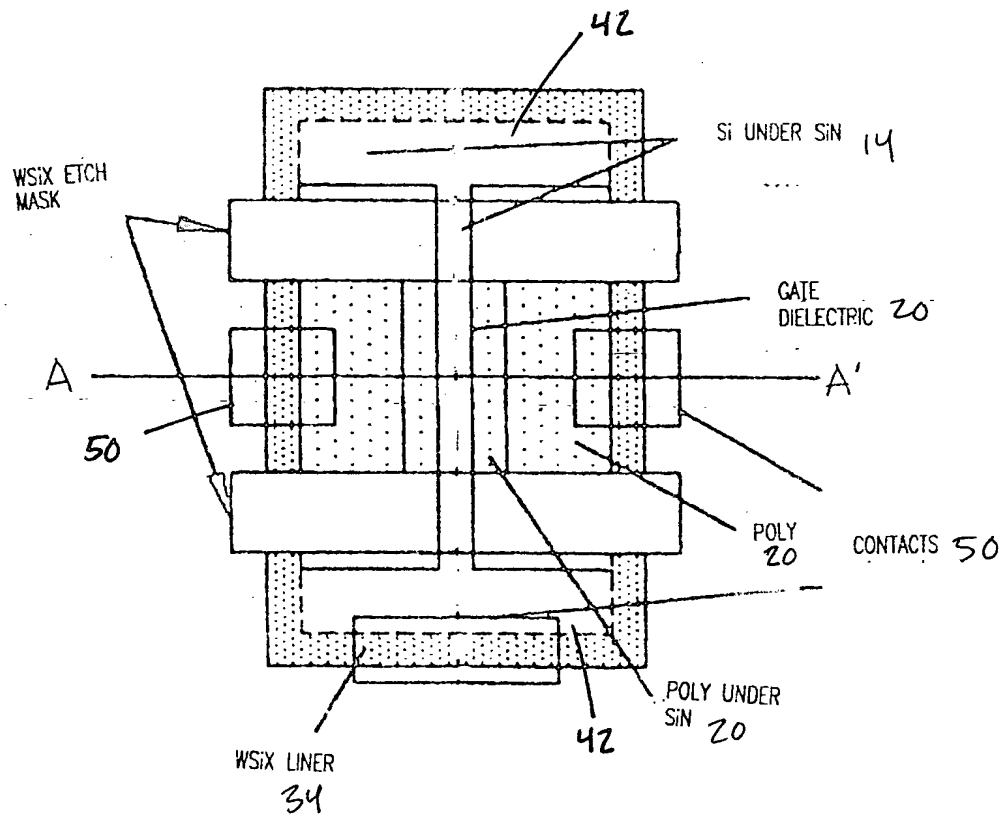


FIG. 5A

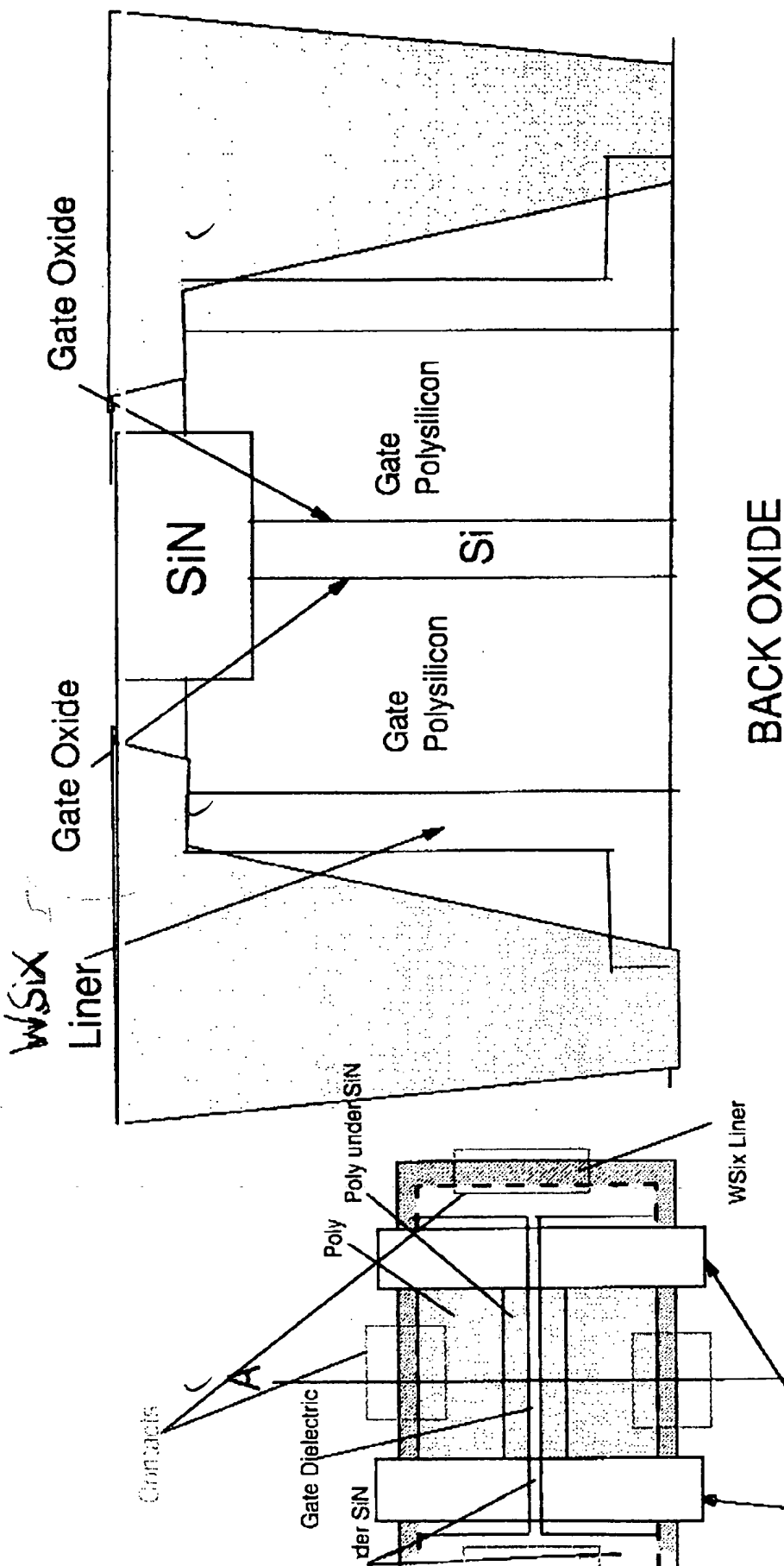


FIGURE 5 (Section AA')

* Standard STI processing is now performed. A damascene gate may be used to contact the gate polysilicon or contacts may be landed in the STI to contact the WSiX liner to make a connection to the gate. The source and drain is contacted with a standard contact process. Note that SiN is left only on top of the regions where the Si is present

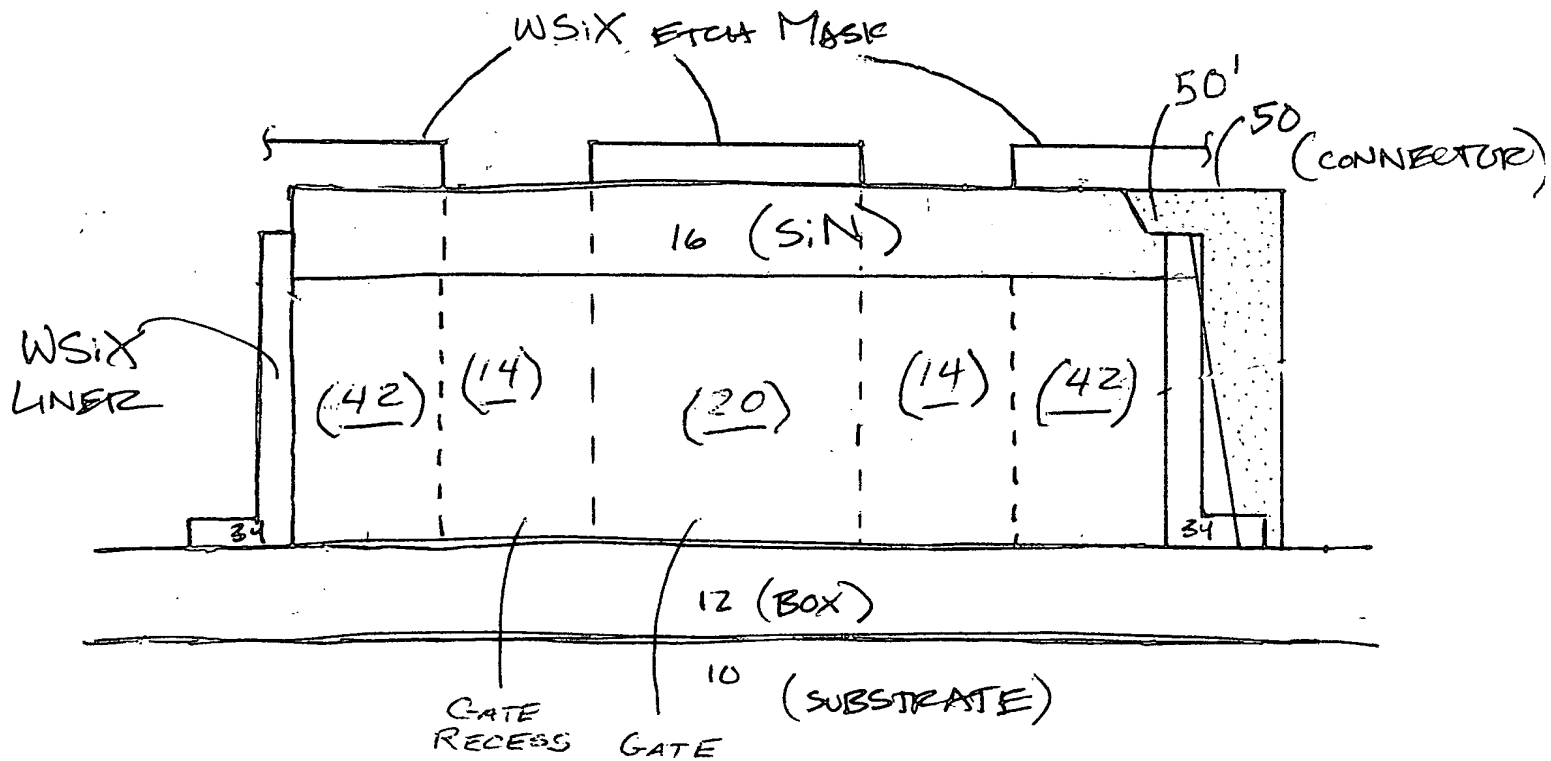


FIG. 5B